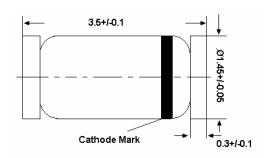
## SILICON SCHOTTKY BARRIER DIODES

for general purpose applications



Glass case MiniMELF Dimensions in mm

## Absolute Maximum Ratings (T<sub>a</sub> = 25°C)

	Symbol	Value	Unit
Peak Reverse Voltage	V <sub>RRM</sub>	40	V
Continuous Forward Current	١ <sub>F</sub>	30	mA
Repetitive Peak Forward Current t <sub>p</sub> $\leq$ 1s; $\delta \leq$ 0.5	I <sub>FRM</sub>	150	mA
Repetitive Peak Forward Current t <sub>p</sub> =1s	I <sub>FSM</sub>	500	mA
Junction Temperature	Tj	125	°C
Storage Temperature Range	Ts	-65 to +150	°C

	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient	R <sub>thj-a</sub>	320	K/W







Dated : 09/12/2004

## Characteristics at T<sub>amb</sub> = 25°C

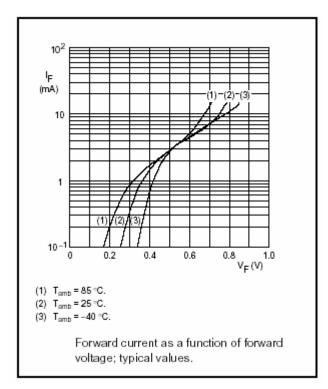
	Symbol	Min.	Тур.	Max.	Unit
Forward Voltage					
at $I_F = 0.1 \text{mA}$	V <sub>F</sub>	-	-	0.33	V
at $I_F = 1 m A$	V <sub>F</sub>	-	-	0.41	V
at $I_F = 15mA$	$V_{F}$	-	-	1	V
Leakage Current					
at $V_R = V_{RMAX}$	I <sub>R</sub>	-	-	200	nA
Junction Capacitance					
at $V_R = 2V$ , f = 1MHz	C <sub>tot</sub>	-	-	1.6	pF

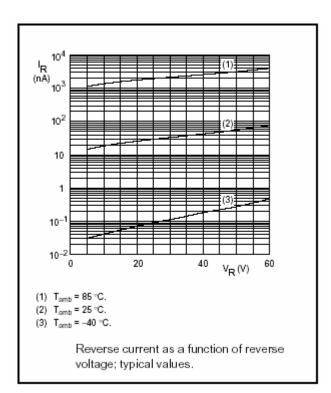


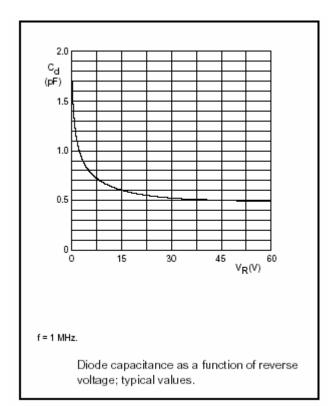




Dated : 09/12/2004













Dated : 09/12/2004